

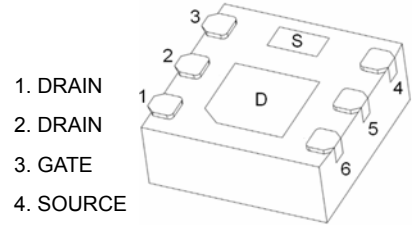


DFNWB2×2-6L Plastic-Encapsulate MOSFETS

M1206 P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-12V	30 mΩ@-4.5V	-6A
	40 mΩ@-2.5V	
	60 mΩ@-1.8V	

DFNWB2×2-6L



1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

DESCRIPTION

The M1206 uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge and operation with low gate voltage. This device is suitable for use as a load switching application and a wide variety of other applications.

FEATURES

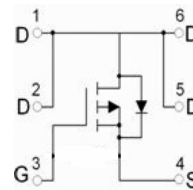
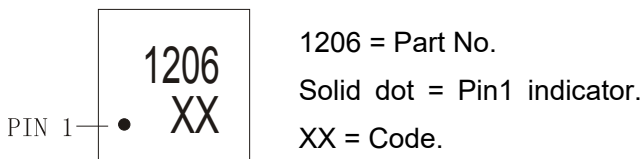
- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

APPLICATIONS

- PWM application
- Load switch
- Battery charge in cellular handset

.....A5F?B;

Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 8	
Drain Current-Continuous	I_D	-6	A
Drain Current-Pulsed	I_{DM}^*	-20	
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	$^\circ\text{C}$

*Repetitive rating: Pluse width limited by junction temperature.

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

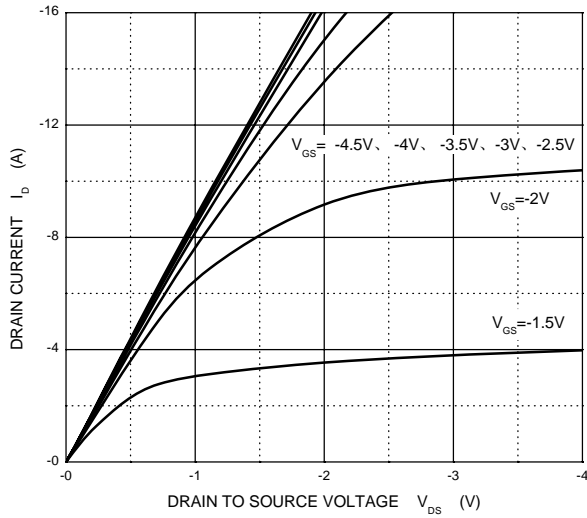
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-12			V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.5		-0.9	
Gate-source leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -8V, V_{GS} = 0V$			-1	μA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -3.5A$		30	45	m Ω
		$V_{GS} = -2.5V, I_D = -3A$		40	60	
		$V_{GS} = -1.8V, I_D = -2.0A$		60	90	
Forward transconductance ^a	g_{fs}	$V_{DS} = -5V, I_D = -4.1A$	6			S
Dynamic						
Input capacitance ^{b,c}	C_{iss}	$V_{DS} = -4V, V_{GS} = 0V, f = 1MHz$		740		pF
Output capacitance ^{b,c}	C_{oss}			290		
Reverse transfer capacitance ^{b,c}	C_{rss}			190		
Total gate charge ^b	Q_g	$V_{DS} = -4V, V_{GS} = -4.5V, I_D = -4.1A$		7.8	15	nC
		$V_{DS} = -4V, V_{GS} = -2.5V, I_D = -4.1A$		4.5	9	
Gate-source charge ^b	Q_{gs}			1.2		
Gate-drain charge ^b	Q_{gd}			1.6		
Gate resistance ^{b,c}	R_g	$f = 1MHz$	1.4	7	14	Ω
Turn-on delay time ^{b,c}	$t_{d(on)}$	$V_{DD} = -4V, R_L = 1.2\Omega, I_D \approx -3.3A, V_{GEN} = -4.5V, R_g = 1\Omega$		13	20	ns
Rise time ^{b,c}	t_r			35	53	
Turn-off Delay time ^{b,c}	$t_{d(off)}$			32	48	
Fall time ^{b,c}	t_f			10	20	
Turn-on delay time ^{b,c}	$t_{d(on)}$	$V_{DD} = -4V, R_L = 1.2\Omega, I_D \approx -3.3A, V_{GEN} = -8V, R_g = 1\Omega$		5	10	
Rise time ^{b,c}	t_r			11	17	
Turn-off delay time ^{b,c}	$t_{d(off)}$			22	33	
Fall time ^{b,c}	t_f			16	24	
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S				-6	A
Pulse diode forward current ^a	I_{SM}				-20	
Body diode voltage	V_{SD}	$I_F = -3.3A$			-1.2	V

Note :

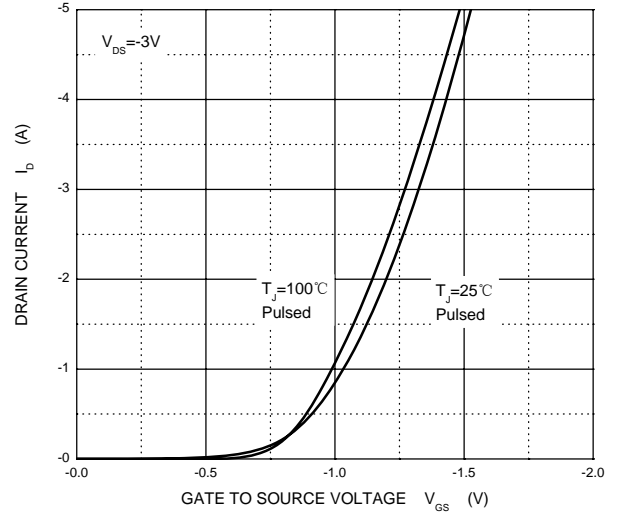
- a. Pulse Test ; Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. These parameters have no way to verify.

Typical Characteristics

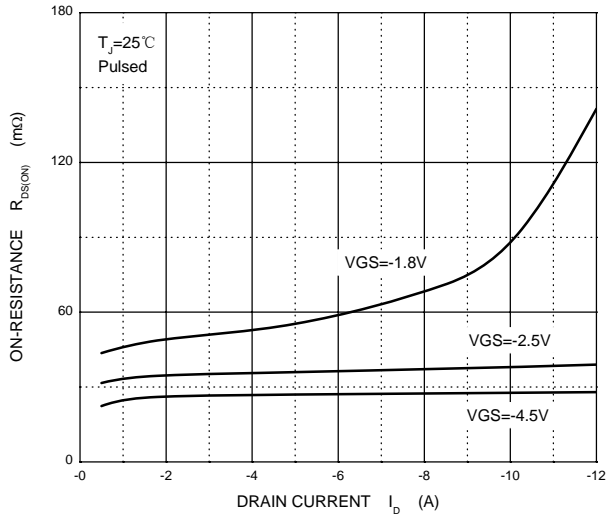
Output Characteristics



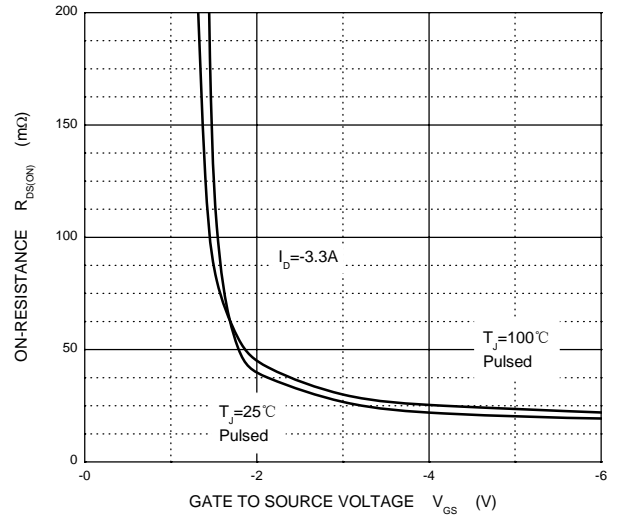
Transfer Characteristics



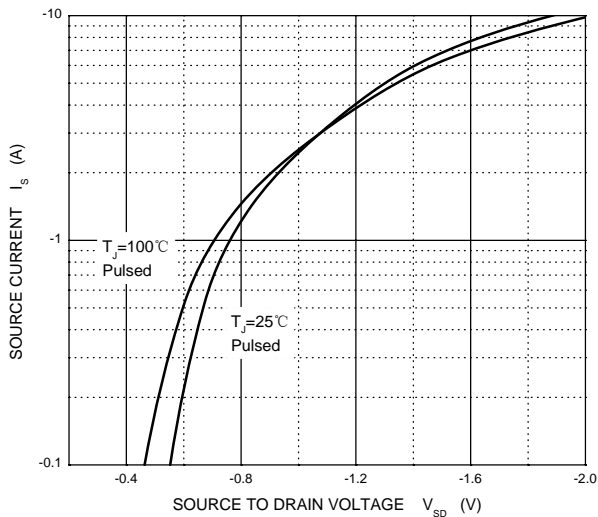
$R_{DS(ON)}$ — I_D



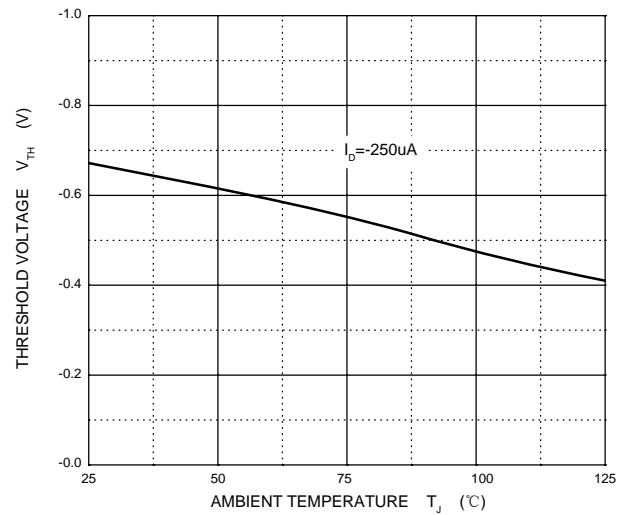
$R_{DS(ON)}$ — V_{GS}



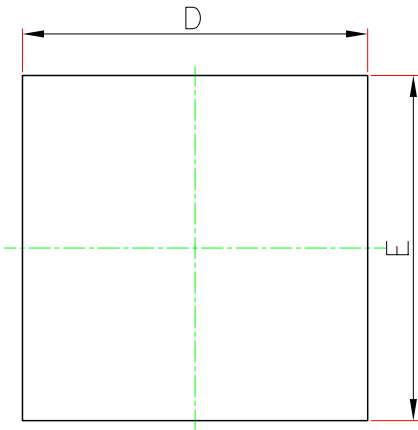
I_S — V_{SD}



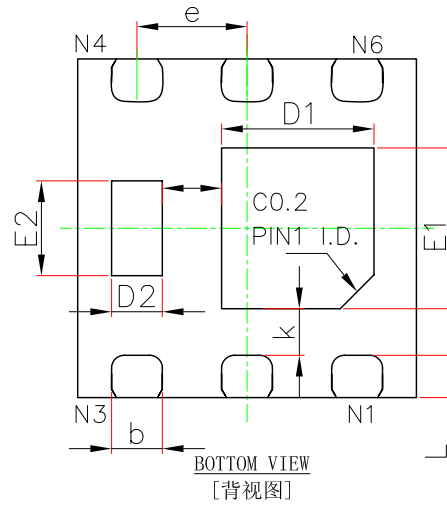
Threshold Voltage



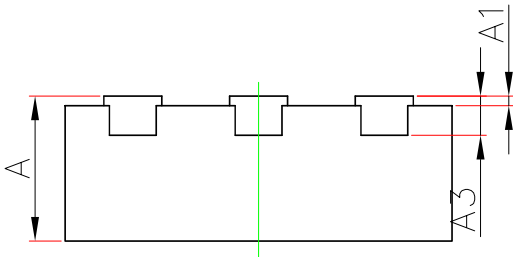
DFNWB2×2-6L-J Package Outline Dimensions



TOP VIEW
[顶视图]



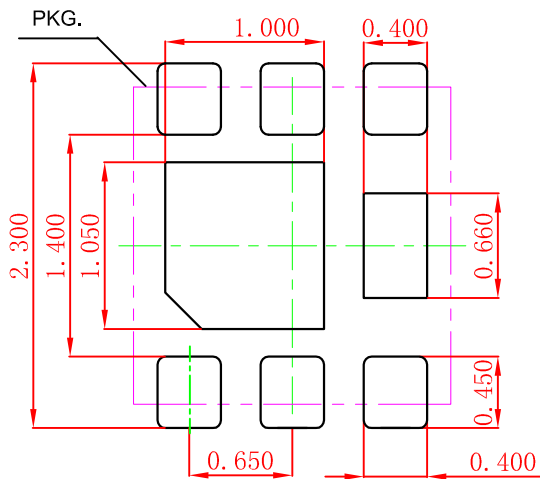
BOTTOM VIEW
[背视图]



SIDE VIEW
[侧视图]

Symbols	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
b	0.250	0.350	0.010	0.014
e	0.650BSC.		0.026BSC.	
k	0.275REF.		0.011REF.	
k1	0.350REF.		0.014REF.	
L	0.174	0.326	0.007	0.013

DFNWB2×2-6L-J Suggested Pad Layout

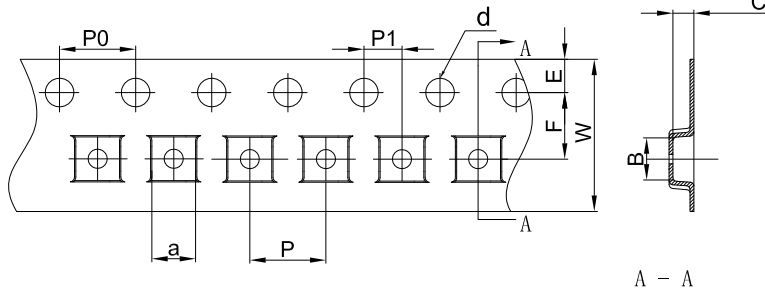


Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.050\text{mm}$.
3. The pad layout is for reference purposes only.

DFNWB2X2-6L Tape and Reel

DFNWB2×2-6L Embossed Carrier Tape



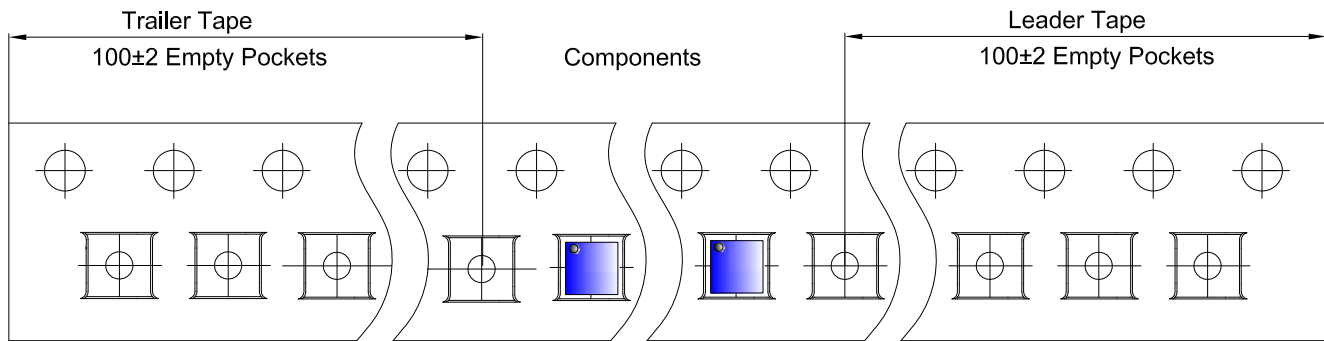
Packaging Description:

DFNWB2×2-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

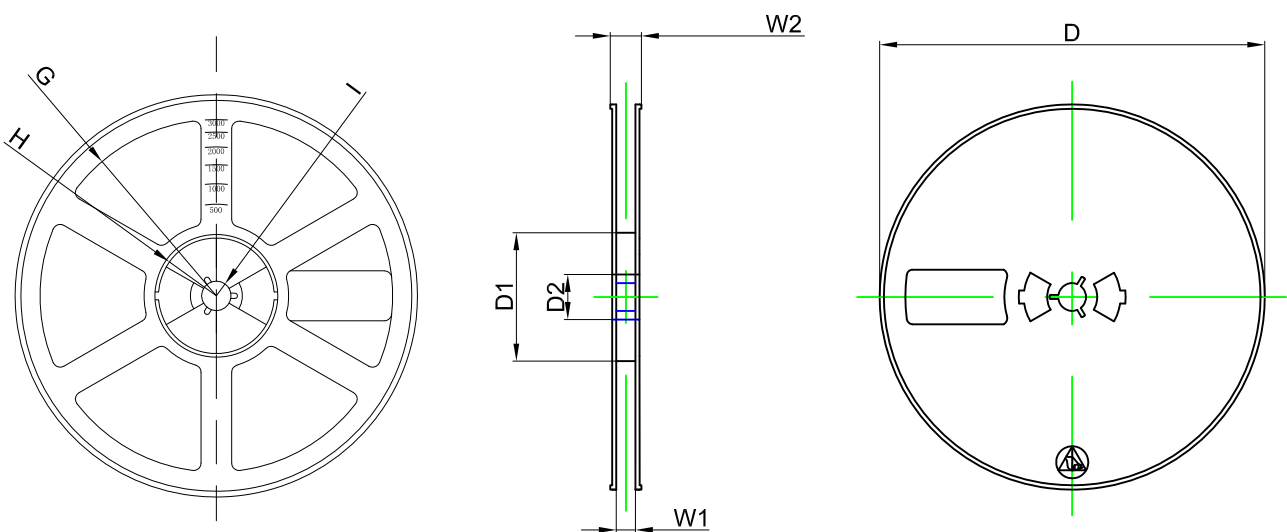
Dimensions are in millimeter

Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFNWB2×2-6L	2.30	2.30	1.10	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

DFNWB2×2-6L Tape Leader and Trailer



DFNWB2×2-6L Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	